

Attorney's Docket No.: 07977/017002/US2968C1D1

forming an insulating film on said crystalline semiconductor film;

D1
cont. introducing a dopant impurity into said crystalline semiconductor film through said insulating film by an ion doping without mass separation; and

Sub E1 annealing said crystalline semiconductor film,

wherein a peak of a concentration profile of said dopant impurity is located in said insulating film.

22. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

D2
Sub E1 forming a crystalline semiconductor film on an insulating surface;

forming an insulating film on said crystalline semiconductor film;

introducing a dopant impurity into said crystalline semiconductor film through said insulating film by an ion doping without mass separation; and

annealing said crystalline semiconductor film,

wherein a peak of a concentration profile of said dopant impurity is located above said insulating surface.

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Please add the following new claims 83-86.

Sub E1
D 3

--83. (NEW) A method according to claim 43 wherein said ion doping is performed without mass separation.

84. (NEW) A method according to claim 52 wherein said ion doping is performed without mass separation.

85. (NEW) A method according to claim 65 wherein said ion doping is performed without mass separation.

86. (NEW) A method according to claim 74 wherein said ion doping is performed without mass separation. --